

**METHOD FOR IMPROVEMENT OF EDGE
BREAKDOWN CAUSED BY EDGE
ELECTRICAL FIELD AT A TUNNEL
OXIDE OF A HIGH-DENSITY FLASH
MEMORY BY A SHIELDED BIRD'S BEAK**

ABSTRACT OF THE DISCLOSURE

To improve the edge breakdown caused by edge electrical field at the tunnel oxide of high-density flash memory, a bird's beak is formed at the edge of the active region of the flash memory to prevent the corner of the tunnel oxide layer formed later on the active region from being excessively sharp, which will result in localized intense electrical field, and further lead to breakdown caused by the edge electrical field.